

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant:

Qi Xiang

Title:

SILICON ON INSULATOR SUBSTRATE

HAVING IMPROVED THERMAL

CONDUCTIVITY AND METHOD OF ITS

FORMATION

Application No.:

10/658,668

Filing Date:

9 September 2003

Examiner:

H. TRINH

Art Unit:

2814

REPLY TO OFFICIAL ACTION OF 1 JUNE 2005 UNDER 37 CFR §1.116

Mail Stop AF Commissioner for Patents PO Box 1450 Alexandria, VA 22313-1450

Sir:

Applicant hereby replies to the official action mailed 1 June 2005.

Reconsideration in view of the following amendments and remarks is requested.